

## 2425-25 25 WATT, 24V, Class C Microwave 2410-2470 MHz

<b>GENERAL DESCRIPTION</b> The <b>2425-25</b> is a common base bip of Class C RF output power over th specifically designed for microway It includes input and output match ballasting to provide high reliability	CASE OUTLINE 55AP Common Base Narrow Lead	
<b>ABSOLUTE MAXIMUM F</b> <b>Power Dissipation</b> Device Dissipation @25°C ( $P_d$ ) Thermal Resistance ( $\theta_{IC}$ )		
Voltage and Current Collector-Emitter Voltage Emitter-Base Voltage Collector Current Temperatures Storage Temperature Operating Junction Temperature	48V 3.5V 3A -65 to +200°C +200°C	

## **ELECTRICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
BVebo	Emitter-Base Breakdown(open)	Ie=25mA	3.5			V
BVces	Collector-Emitter Breakdown(shorted)	Ic=160mA	48			V
$h_{\rm FE}$	DC Current Gain	Ic=160mA, Vce=5V	10		100	β

## FUNCTIONAL CHARACTERISTICS @ 25°C

G <sub>PB</sub>	Common Base Power Gain	$V_{cc} = 24V, F = 2410-2470 \text{ MHz}, P_{out}=25W$	7.5	8		dB
$\eta_{c}$	Collector Efficiency	$V_{cc} = 24V, F = 2410-2470 \text{ MHz}, P_{out}=25W$	47	49		%
VSWR	Output Load Mismatch	$V_{cc} = 24V, F = 2410-2470 \text{ MHz}, P_{out}=25W$			3:1	Ψ
$Z_{in}(1)$	Series Source Impedance	V <sub>cc</sub> =24V,F=2410,2440,2470 MHz,P <sub>out</sub> =25W	8.6- j19.7	8.4- j19.1	8.2- j18.5	Ω
$Z_{out}(2)$	Series Load Impedance	V <sub>cc</sub> =24V,F=2410,2440,2470 MHz,P <sub>out</sub> =25W	6.1- j5.7	6.1- j5.5	6.1- j5.2	Ω

(1) Circuit source impedance (@ the device input) at which the device operates.

(2) Optimum load impedance into which the device output operates.

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